

PSMN013-100ES

N-channel 100V 13.9m Ω standard level MOSFET in I2PAK. Rev. 3 — 29 September 2011 Product data s

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement MOSFET in I2PAK package qualified to 175C. This product is designed and qualified for use in a wide range of industrial, communications and domestic equipment.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- DC-to-DC converters
- Load switching

- Motor control
- Server power supplies

1.4 Quick reference data

Table 1. Quick reference data

Table 1.	Quick reference da	ta					
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	T_{mb} = 25 °C; V_{GS} = 10 V; see <u>Figure 1</u>	[1]	-	-	68	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	170	W
Tj	junction temperature			-55	-	175	°C
Static cha	racteristics						
R _{DSon}	drain-source on-state	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A};$ $T_j = 100 \text{ °C}; \text{ see } \frac{\text{Figure 11}}{\text{ or } 100 \text{ or } $		-	-	25	mΩ
	resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	[2]	-	11	13.9	mΩ
Dynamic o	characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $V_{DS} = 50 \text{ V}; \text{see } \underline{\text{Figure 14}};$ $\text{see } \underline{\text{Figure 13}}$		-	17	-	nC



Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Q _{G(tot)}	total gate charge	V_{GS} = 10 V; I_D = 25 A; V_{DS} = 50 V; see <u>Figure 13</u> ; see <u>Figure 14</u>	-	59	-	nC
Avalanche	Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 68 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω	-	-	127	mJ

- [1] Continuous current is limited by package.
- [2] Measured 3 mm from package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	<u> </u>
3	S	source		e_(巨木)
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT226 (I2PAK)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PSMN013-100ES	I2PAK	plastic single-ended package (I2PAK); TO-262	SOT226

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V_{DGR}	drain-gate voltage	$T_j \le 175 \text{ °C}; T_j \ge 25 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$		-	100	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	$V_{GS} = 10 \text{ V; } T_{mb} = 100 \text{ °C; see } \frac{\text{Figure 1}}{}$	<u>[1]</u>	-	47	Α
		$V_{GS} = 10 \text{ V; } T_{mb} = 25 \text{ °C; see } Figure 1$	<u>[1]</u>	-	68	Α
I _{DM}	peak drain current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	272	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	170	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drain	n diode					
Is	source current	T _{mb} = 25 °C	<u>[1]</u>	-	68	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \mu s$; $T_{mb} = 25 ^{\circ}C$		-	272	Α
Avalanche re	uggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; I_D = 68 A; $V_{sup} \le$ 100 V; unclamped; R_{GS} = 50 Ω		-	127	mJ

[1] Continuous current is limited by package.

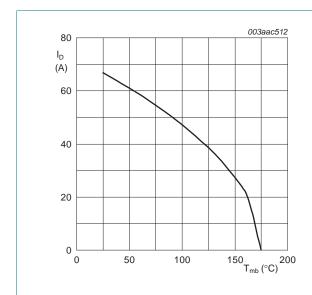


Fig 1. Continuous drain current as a function of mounting base temperature

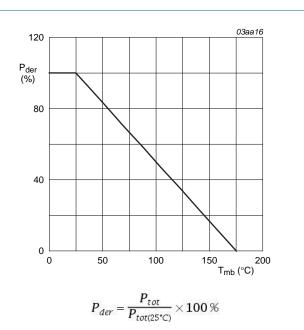


Fig 2. Normalized total power dissipation as a function of mounting base temperature

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 3	-	0.5	0.9	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in free air	-	60	-	K/W

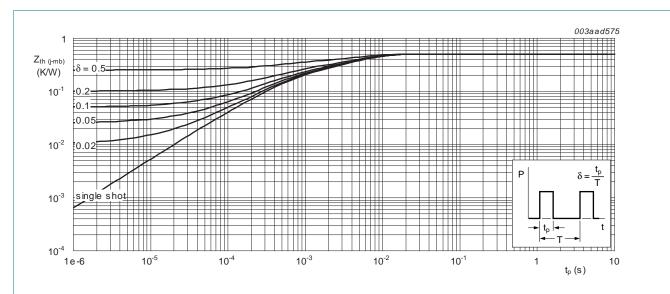


Fig 3. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

6. Characteristics

Table 6. Characteristics

Table 6.	Characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static cha	racteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$!	90	-	-	V
		$I_D = 0.25$ mA; $V_{GS} = 0$ V; $T_j = 25$ °C		100	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 9</u>		1	-	-	V
	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see <u>Figure 10</u> ; see <u>Figure 9</u>		2	3	4	V	
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 10	,	-	-	4.8	V
I _{DSS}	drain leakage current	$V_{DS} = 100 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ °C}$		-	-	100	μΑ
		V _{DS} = 100 V; V _{GS} = 0 V; T _j = 25 °C	,	-	0.06	2	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$,	-	10	100	nΑ
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$		-	10	100	nΑ
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 175 ^{\circ}\text{C};$ see <u>Figure 11</u>		-	30	38.9	mΩ
	$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 100 \text{ °C};$ see Figure 11	,	•	-	25	mΩ	
		$V_{GS} = 10 \text{ V}; I_D = 15 \text{ A}; T_j = 25 ^{\circ}\text{C};$ see Figure 12; see Figure 11	[1]	•	11	13.9	mΩ
R_G	internal gate resistance (AC)	f = 1 MHz		•	1	-	Ω
Dynamic o	characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	,	•	59	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$		-	47.6	-	nC
Q_{GS}	gate-source charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 13; see Figure 14	,	-	13.8	-	nC
Q _{GS(th)}	pre-threshold gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 50 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14	,	•	9.2	-	nC
Q _{GS(th-pl)}	post-threshold gate-source charge		,	•	4.6	-	nC
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}$; $V_{DS} = 50 \text{ V}$; $V_{GS} = 10 \text{ V}$; see Figure 14; see Figure 13	,	•	17	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	V _{DS} = 50 V; see <u>Figure 14</u> ; see <u>Figure 13</u>	,	-	4.4	-	V
C _{iss}	input capacitance	$V_{DS} = 50 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$		-	3195	-	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>		-	221	-	pF
C _{rss}	reverse transfer capacitance			-	136	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 50 \text{ V}; R_L = 2 \Omega; V_{GS} = 10 \text{ V};$		-	20.7	-	ns
t _r	rise time	$R_{G(ext)} = 4.7 \Omega$; $T_j = 25 °C$		-	25	-	ns
t _{d(off)}	turn-off delay time			-	52.5	-	ns
t _f	fall time			-	24	-	ns

Table 6. Characteristics ... continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 15 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C};$ see Figure 16	-	0.8	1.2	V
t _{rr}	reverse recovery time	$I_S = 25 \text{ A}$; $dI_S/dt = 100 \text{ A/}\mu\text{s}$;	-	52	-	ns
Qr	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$	-	109	-	nC

[1] Measured 3 mm from package.

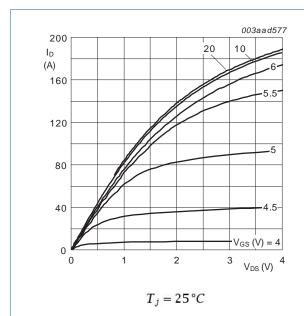


Fig 4. Output characteristics: drain current as a function of drain-source voltage; typical values

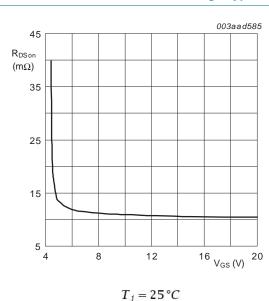


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

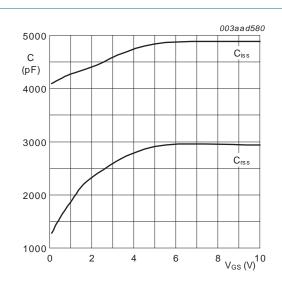


Fig 5. Input and reverse transfer capacitances as a function of gate-source voltage; typical values

 $V_{DS} = 0V; f = 1MHz$

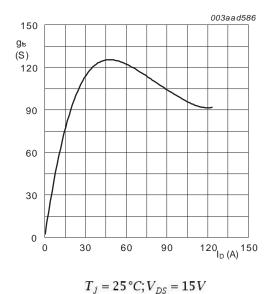


Fig 7. Forward transconductance as a function of drain current; typical values

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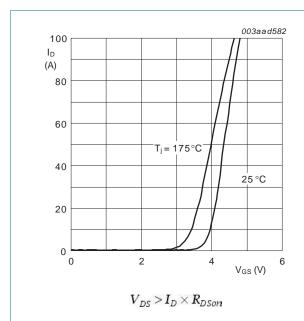


Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values

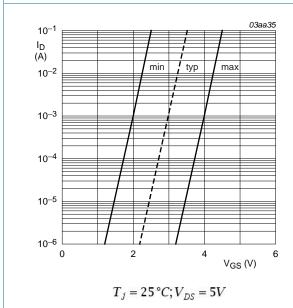


Fig 10. Sub-threshold drain current as a function of gate-source voltage

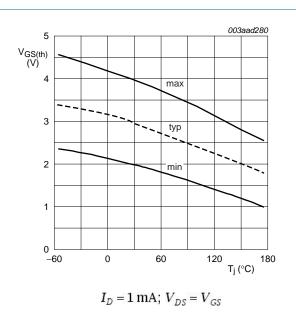


Fig 9. Gate-source threshold voltage as a function of junction temperature

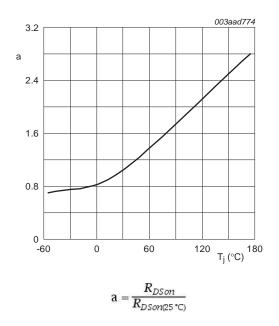


Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature

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N-channel 100V 13.9mΩ standard level MOSFET in I2PAK.

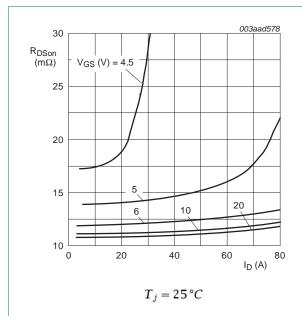


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

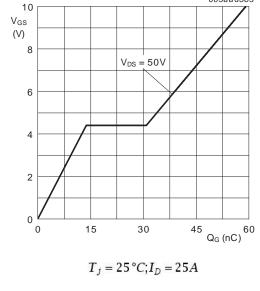


Fig 13. Gate-source voltage as a function of gate charge; typical values

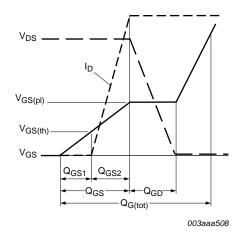


Fig 14. Gate charge waveform definitions

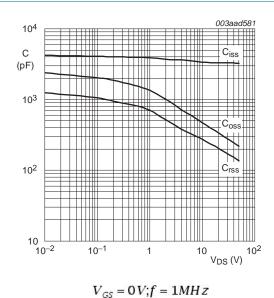


Fig 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

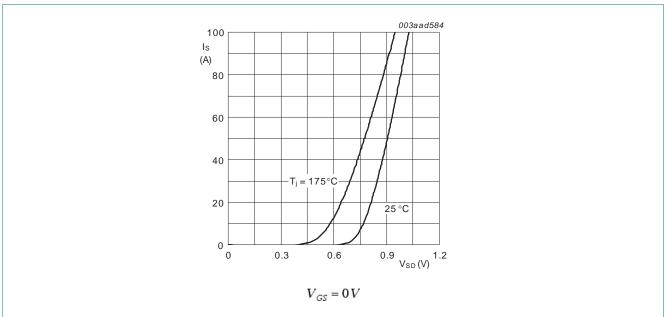


Fig 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

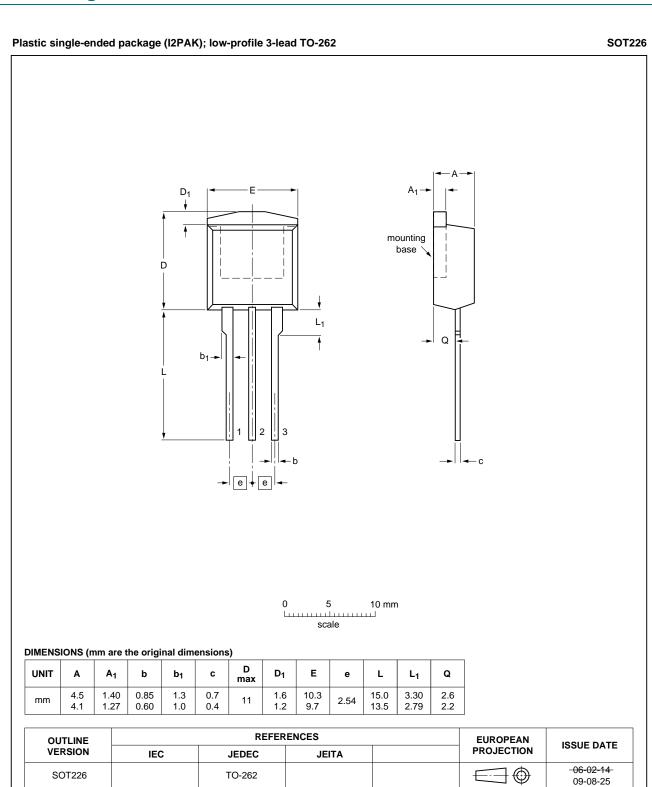


Fig 17. Package outline SOT226 (I2PAK)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-100ES v.3	20110929	Product data sheet	-	PSMN013-100ES v.2
Modifications:	Status changed frVarious changes	om objective to product.		
PSMN013-100ES v.2	20100219	Objective data sheet	-	PSMN013-100ES v.1

9. Legal information

9.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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